

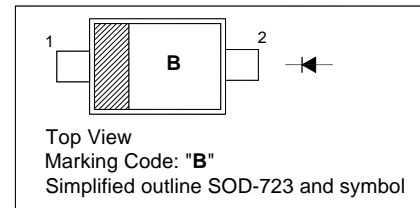
RB521G-30G

Silicon Epitaxial Planar Schottky Barrier Diode

for rectifying small power application

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

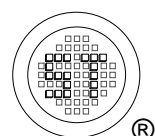


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Average Forward Rectified Current	$I_{F(AV)}$	100	mA
Peak Forward Surge Current (60 Hz for 1 cyc.)	I_{FSM}	1	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	0.35	V
Reverse Current at $V_R = 10\text{ V}$	I_R	10	μA



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Electrical Characteristics Curves

Fig 1. Reverse Characteristics Curve

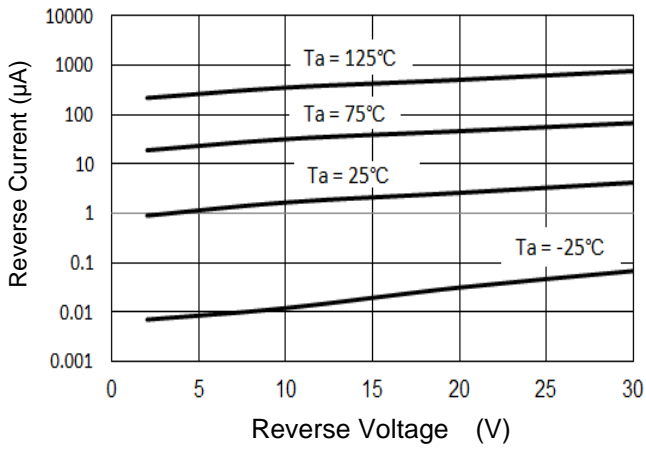


Fig 2. Forward Characteristics Curve

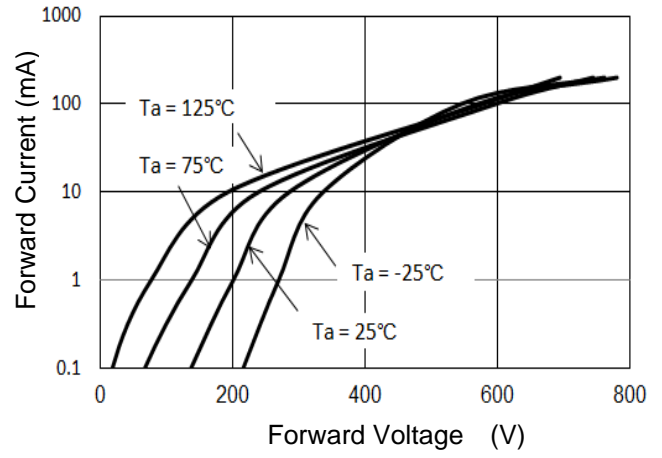
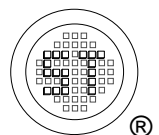
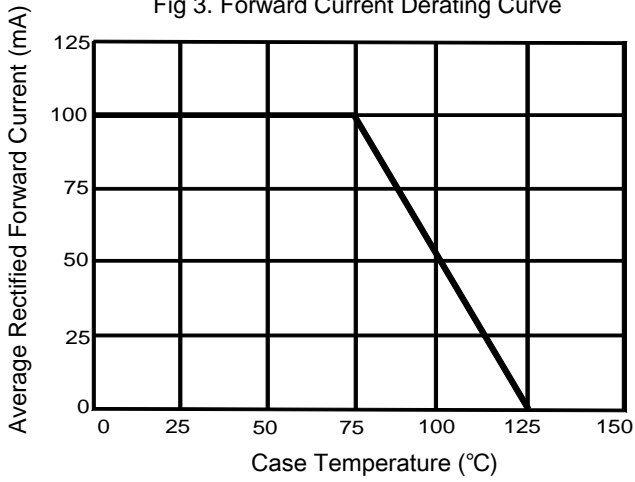


Fig 3. Forward Current Derating Curve

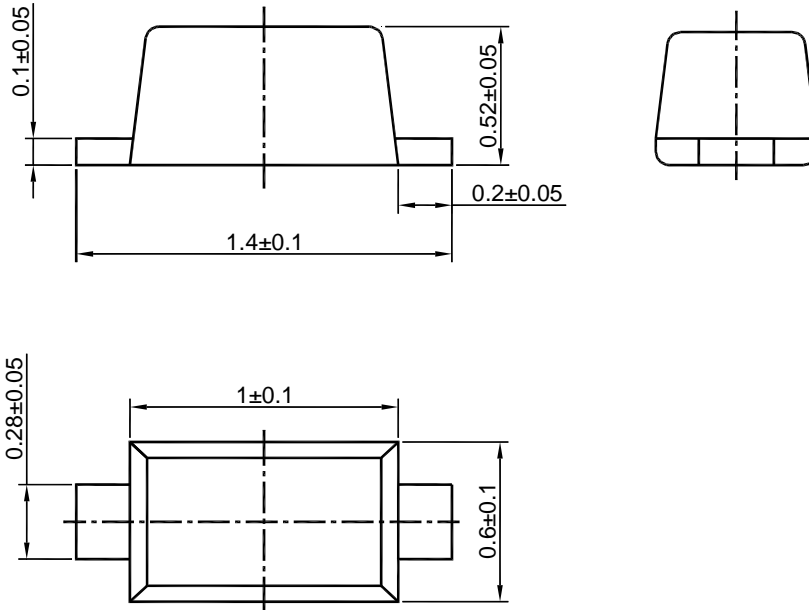


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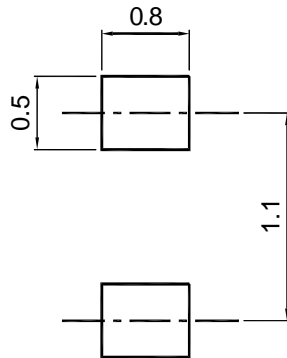
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-723



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOD-723	8	2 ± 0.1	0.079 ± 0.004	178	7	5,000
						10,000

Marking information

" III " = Cathode line

" B " = Part No.

Font type: Arial

